NOMENCLATURE (Continued)

R_c	mid-meridian wafer radius in two-dimensional analysis, in
R_t	wafer radius at anvil-wafer interface, in
R_a	radius at which surface shear stress exceeds wafer material shear **strength,** in
S'	deviator stress tensor, psi
u, w	radial and axial displacements, in
$\dot{u}, \dot{w}$	radial and axial velocities, in/sec
γ_{rz}	shearing strain, in/in
τ_{rz}	shearing stress, psi
$\sigma_r, \sigma_\theta, \sigma_z$	radial, circumferential, and axial normal stress, psi
τ_o	wafer material shear strength, psi
σ_o	yield stress of wafer material, psi
$\bar{\sigma}$	effective wafer material stress during plastic strain, psi
$\epsilon_r, \epsilon_\theta, \epsilon_z$	radial, circumferential, and axial normal strain, in/in
$\bar{\epsilon}$	effective wafer material strain during plastic deformation, sec^{-1}
$\dot{\bar{\epsilon}}$	effective wafer material strain rate during plastic deformation, sec^{-1}
$\epsilon_{\theta c}$	circumferential strain recorded at outer periphery of containing ring, in/in
Δ	wafer centerline deflection, in
δ	deformation occurring at inside diameter of wafer containing ring, in
μ	coefficient of viscosity, lb-sec/in^2
λ	scalar factor appearing in flow law equation, lb-sec/in